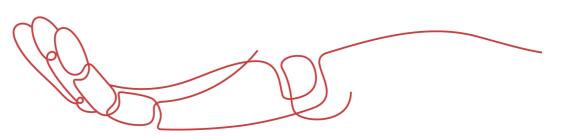




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

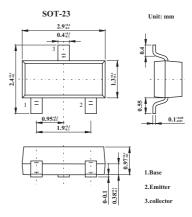
ces Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

NPN Medium Frequency Transistor

■ Features

- Low current (max. 25 mA).
- Low voltage (max. 40 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	Vсво	40	V
Collector-emitter voltage	VCEO	40	V
Emitter-base voltage	Vево	4	V
Collector current	Ic	25	mA
Peak collector current	Ісм	25	mA
Total power dissipation *	Ptot	250	mW
Storage temperature	Tstg	-65 to +150	$^{\circ}$
Junction temperature	Tj	150	$^{\circ}\! \mathbb{C}$
Operating ambient temperature	Ramb	-65 to +150	$^{\circ}\!\mathbb{C}$
Thermal resistance from junction to ambient *	Rth j-a	500	K/W

^{*} Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector cutoff current	Ісво	IE = 0; VcB = 20 V			100	nA
Emitter cutoff current	ІЕВО	Ic = 0; VEB = 4 V			100	nA
DC current gain	hFE	Ic = 1 mA; VcE = 10 V	67		222	
Base to emitter voltage	VBE	Ic = 1 mA; VcE = 10 V	675	725	775	mV
Feedback capacitance	Cre	Ic = 0; VcB = 10 V; f = 1 MHz		0.3		pF
Transition frequency	f⊤	Ic = 1 mA; VcE = 10 V; f = 100 MHz		380		MHz



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